



#### **N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

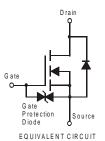
## **Mechanical Data**

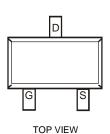
- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Alloy 42
  Leadframe. Solderable per MIL-STD-202, Method 208 <a> § 3</a>
- Weight: 0.006 grams (Approximate)











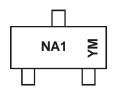
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMG1012UW-7	SOT323	3000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



NA1 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2009	~	20	19	2020	2021	2022	2023	3 20	24	2025	2026
Code	W	?	(	G	Н	I	J	K		L	M	N
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

DMG1012UW Document number: DS31859 Rev. 5 - 2



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Char	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	20	V
Gate-Source Voltage	V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 5)	ID	1.0 0.64	А
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	6	Α

## **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.29	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	425	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout. 6. Repetitive rating, pulse width limited by junction temperature.

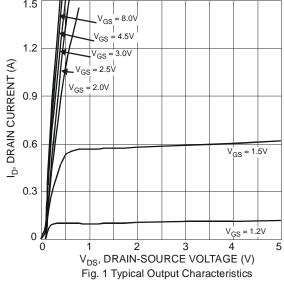
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

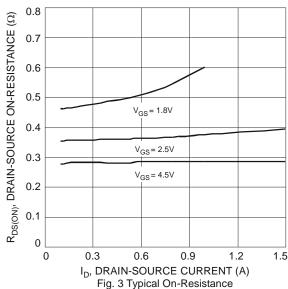
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	•	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	ı	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	$I_{GSS}$	Ī	1	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			0.3	0.45		$V_{GS} = 4.5V, I_D = 600mA$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	0.4	0.6	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
			0.5	0.75		$V_{GS} = 1.8V, I_D = 350mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.4		S	$V_{DS} = 10V, I_{D} = 400mA$	
Diode Forward Voltage	$V_{SD}$	-	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	60.67	-	pF	101/11/	
Output Capacitance	Coss	-	9.68	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	5.37	-	pF	1 = 1.000112	
Total Gate Charge	$Q_g$	-	736.6	-	рC	15/// 40//	
Gate-Source Charge	Qgs	-	93.6	-	рC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	$Q_{gd}$	=	116.6	-	рC	$I_D = 250 \text{mA}$	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	5.1	-	ns	.,,	
Turn-On Rise Time	t <sub>R</sub>	=	7.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	26.7	-	ns	$R_L = 47\Omega$ , $R_G = 10\Omega$ , $I_D = 200\text{mA}$	
Turn-Off Fall Time	t <sub>F</sub>	-	12.3	-	ns	1D = 200111A	

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

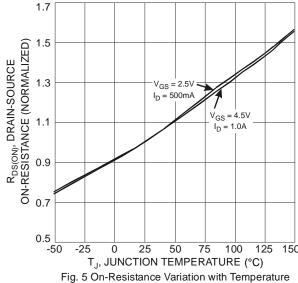
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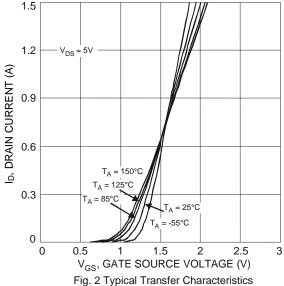






vs. Drain Current and Gate Voltage





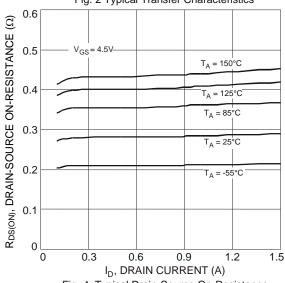


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

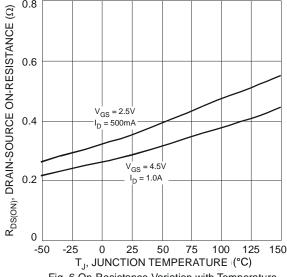


Fig. 6 On-Resistance Variation with Temperature



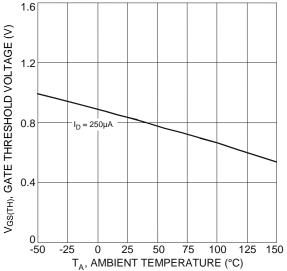
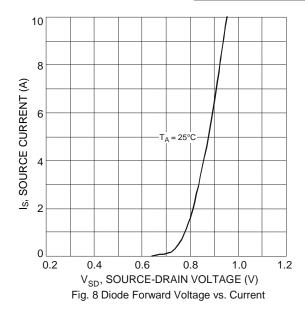
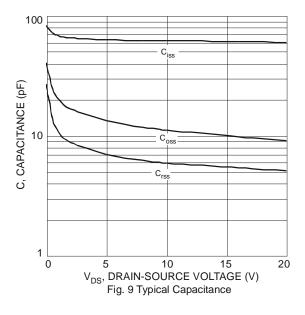
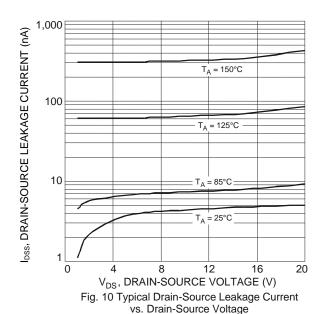


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







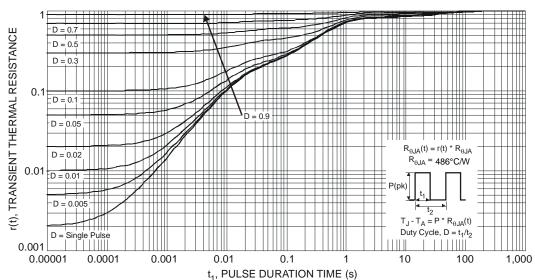


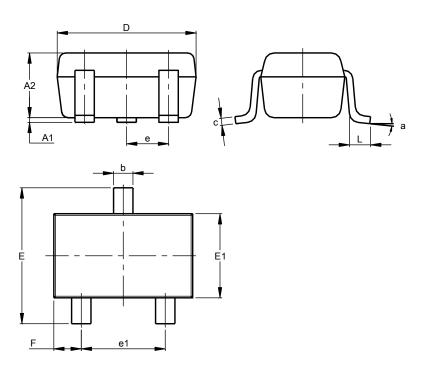
Fig. 11 Transient Thermal Response



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT323**

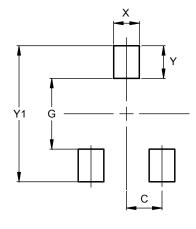


SOT323							
Dim	Min Max Typ						
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT323



Dimensions	Value (in mm)			
С	0.650			
G	1.300			
X	0.470			
Y	0.600			
Y1	2.500			



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